

Title (en)
ETCHING PROCESS

Title (de)
ÄTZVERFAHREN

Title (fr)
PROCESSUS DE GRAVURE

Publication
EP 3075003 A1 20161005 (EN)

Application
EP 14825103 A 20141119

Priority
• EP 13194774 A 20131128
• EP 2014075023 W 20141119
• EP 14825103 A 20141119

Abstract (en)
[origin: EP2879165A1] Processes for the manufacture of devices including microelectromechanical systems comprising a step in which a substrate is etched using an etching agent prepared from SF₄ are disclosed.

IPC 8 full level
H01L 21/3065 (2006.01); **C23C 16/44** (2006.01); **C23F 1/00** (2006.01)

CPC (source: EP)
C23F 4/00 (2013.01); **H01L 21/3065** (2013.01); **H01L 21/3116** (2013.01); **H01L 21/32136** (2013.01)

Citation (search report)
See references of WO 2015078749A1

Citation (examination)
PATEAU AMAND ET AL: "Modeling of inductively coupled plasma SF₆/O₂/Ar plasma discharge: Effect of O₂ on the plasma kinetic properties", JOURNAL OF VACUUM SCIENCE AND TECHNOLOGY: PART A, AVS /AIP, MELVILLE, NY., US, vol. 32, no. 2, 1 January 1901 (1901-01-01), XP012184288, ISSN: 0734-2101, [retrieved on 19010101], DOI: 10.1116/1.4853675

Designated contracting state (EPC)
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Designated extension state (EPC)
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DOCDB simple family (publication)
EP 2879165 A1 20150603; EP 3075003 A1 20161005; WO 2015078749 A1 20150604

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EP 13194774 A 20131128; EP 14825103 A 20141119; EP 2014075023 W 20141119